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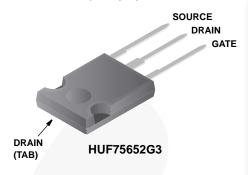


Data Sheet October 2013

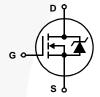
N-Channel UltraFET Power MOSFET 100 V, 75 A, 8 $m\Omega$

Packaging

JEDEC TO-247



Symbol



Features

- Ultra Low On-Resistance
 - $r_{DS(ON)} = 0.008\Omega$, $V_{GS} = 10V$
- Simulation Models
 - Temperature Compensated PSPICE® and SABER™ Electrical Models
 - Spice and SABER Thermal Impedance Models
 - www.fairchildsemi.com
- · Peak Current vs Pulse Width Curve
- UIS Rating Curve

Ordering Information

PART NUMBER	PACKAGE	BRAND
HUF75652G3	TO-247	75652G

Absolute Maximum Ratings $T_C = 25^{\circ}C$, Unless Otherwise Specified		
	HUF75652G3	UNITS
Drain to Source Voltage (Note 1)	100	V
Drain to Gate Voltage ($R_{GS} = 20k\Omega$) (Note 1)	100	V
Gate to Source Voltage	±20	V
$ \begin{array}{llllllllllllllllllllllllllllllllllll$	75 75 Figure 4	A A
Pulsed Avalanche RatingUIS	Figure 6	
Power Dissipation (Note 2)	515 3.44	W W/ ^o C
Operating and Storage Temperature	-55 to 175	°C
Maximum Temperature for Soldering Leads at 0.063in (1.6mm) from Case for 10s	300 260	°C
NOTES:		

^{1.} $T_J = 25^{\circ}C$ to $150^{\circ}C$.

CAUTION: Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.

Product reliability information can be found at http://www.fairchildsemi.com/products/discrete/reliability/index.html
For severe environments, see our Automotive HUFA series.

All Fairchild semiconductor products are manufactured, assembled and tested under ISO9000 and QS9000 quality systems certification.

HUF75652G3

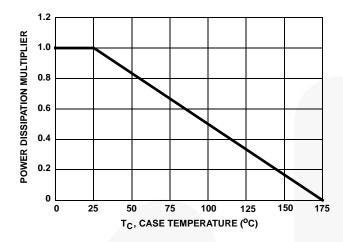
Electrical Specifications $T_C = 25^{\circ}C$, Unless Otherwise Specified

PARAMETER	SYMBOL	TES ⁻	CONDITIONS	MIN	TYP	MAX	UNITS
OFF STATE SPECIFICATIONS						l	
Drain to Source Breakdown Voltage	BV _{DSS}	$I_D = 250\mu A, V_{GS} = 0$	V (Figure 11)	100	-	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 95V, V _{GS} = 0	V	-	-	1	μΑ
		V _{DS} = 90V, V _{GS} = 0	V, T _C = 150 ^o C	-	-	250	μΑ
Gate to Source Leakage Current	I _{GSS}	V _{GS} = ±20V		-	-	±100	nA
ON STATE SPECIFICATIONS							
Gate to Source Threshold Voltage	V _{GS(TH)}	$V_{GS} = V_{DS}, I_D = 250$	DμA (Figure 10)	2	-	4	V
Drain to Source On Resistance	r _{DS(ON)}	I _D = 75A, V _{GS} = 10\	/ (Figures 9)	-	0.0067	0.008	Ω
THERMAL SPECIFICATIONS							
Thermal Resistance Junction to Case	$R_{\theta JC}$	TO-247		-	-	0.29	oC/W
Thermal Resistance Junction to Ambient	$R_{\theta JA}$			-	-	30	°C/W
SWITCHING SPECIFICATIONS (VGS =	: 10V)						1
Turn-On Time	ton	V_{DD} = 50V, I_{D} = 75A, V_{GS} = 10V, R_{GS} = 2.0 Ω		-	-	320	ns
Turn-On Delay Time	t _d (ON)			-	18.5	-	ns
Rise Time	t _r			-	195	-	ns
Turn-Off Delay Time	t _d (OFF)			-	80	-	ns
Fall Time	t _f			-	190	-	ns
Turn-Off Time	tOFF			-	-	410	ns
GATE CHARGE SPECIFICATIONS					1		
Total Gate Charge	Q _{g(TOT)}	V _{GS} = 0V to 20V	V _{DD} = 50V,	-	393	475	nC
Gate Charge at 10V	Q _{g(10)}	V _{GS} = 0V to 10V	$I_D = 75A,$ $I_{g(REF)} = 1.0mA$	-	211	255	nC
Threshold Gate Charge	Q _{g(TH)}	V _{GS} = 0V to 2V	(Figure 13)	-	14	16.5	nC
Gate to Source Gate Charge	Q _{gs}			-	26	-	nC
Gate to Drain "Miller" Charge	Q _{gd}			-	74	-	nC
CAPACITANCE SPECIFICATIONS				1		1	
Input Capacitance	C _{ISS}	V _{DS} = 25V, V _{GS} = 0V, f = 1MHz (Figure 12)		-	7585	-	pF
Output Capacitance	C _{OSS}			-	2345	-	pF
Reverse Transfer Capacitance	C _{RSS}			-	630	-	pF

Source to Drain Diode Specifications

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
Source to Drain Diode Voltage	V _{SD}	I _{SD} = 75A	-	-	1.25	V
		I _{SD} = 35A	-	-	1.00	V
Reverse Recovery Time	t _{rr}	$I_{SD} = 75A$, $dI_{SD}/dt = 100A/\mu s$	-	-	150	ns
Reverse Recovered Charge	Q _{RR}	$I_{SD} = 75A$, $dI_{SD}/dt = 100A/\mu s$	-	-	490	nC

Typical Performance Curves





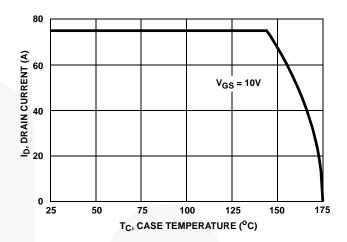


FIGURE 2. MAXIMUM CONTINUOUS DRAIN CURRENT vs CASE TEMPERATURE

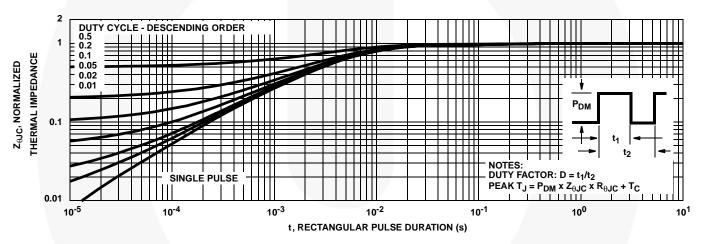


FIGURE 3. NORMALIZED MAXIMUM TRANSIENT THERMAL IMPEDANCE

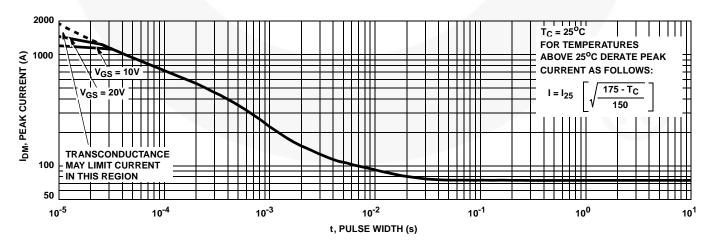


FIGURE 4. PEAK CURRENT CAPABILITY

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Typical Performance Curves (Continued)

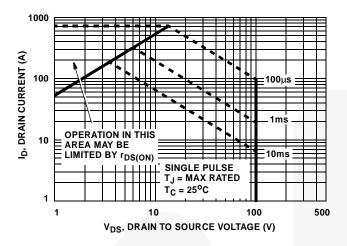


FIGURE 5. FORWARD BIAS SAFE OPERATING AREA

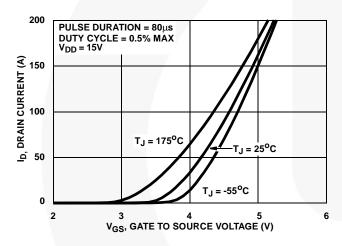


FIGURE 7. TRANSFER CHARACTERISTICS

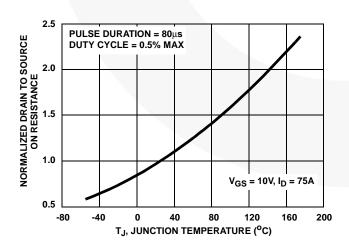
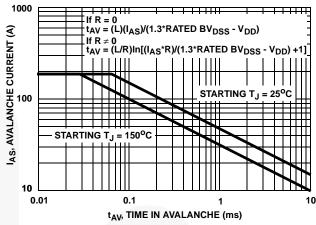


FIGURE 9. NORMALIZED DRAIN TO SOURCE ON RESISTANCE vs JUNCTION TEMPERATURE



NOTE: Refer to Fairchild Application Notes AN9321 and AN9322.

FIGURE 6. UNCLAMPED INDUCTIVE SWITCHING CAPABILITY

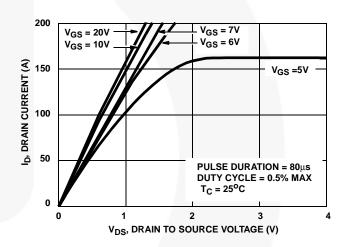


FIGURE 8. SATURATION CHARACTERISTICS

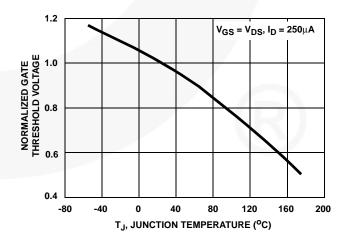
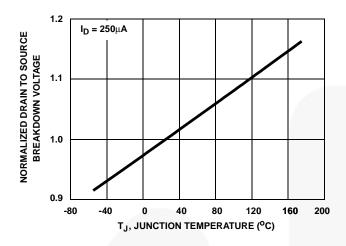


FIGURE 10. NORMALIZED GATE THRESHOLD VOLTAGE vs JUNCTION TEMPERATURE

Typical Performance Curves (Continued)



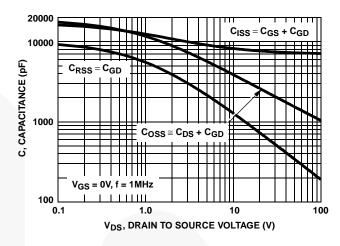
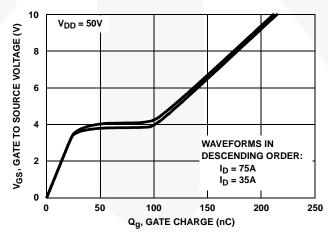


FIGURE 11. NORMALIZED DRAIN TO SOURCE BREAKDOWN VOLTAGE vs JUNCTION TEMPERATURE

FIGURE 12. CAPACITANCE vs DRAIN TO SOURCE VOLTAGE



NOTE: Refer to Fairchild Application Notes AN7254 and AN7260.

FIGURE 13. GATE CHARGE WAVEFORMS FOR CONSTANT GATE CURRENT

Test Circuits and Waveforms

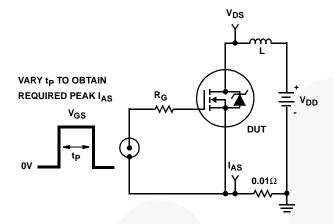


FIGURE 14. UNCLAMPED ENERGY TEST CIRCUIT

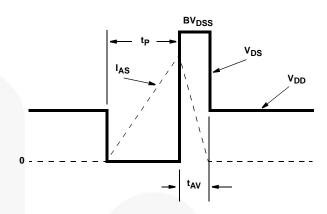


FIGURE 15. UNCLAMPED ENERGY WAVEFORMS

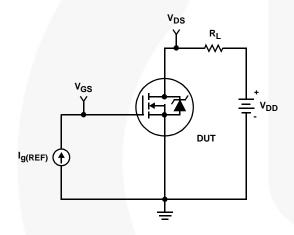


FIGURE 16. GATE CHARGE TEST CIRCUIT

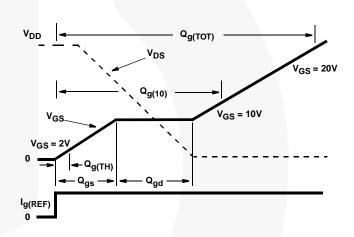


FIGURE 17. GATE CHARGE WAVEFORMS

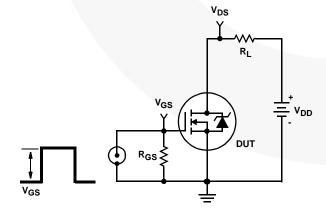


FIGURE 18. SWITCHING TIME TEST CIRCUIT

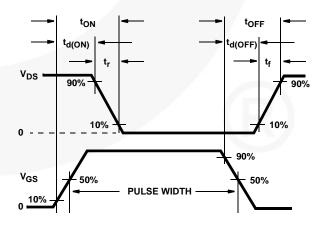
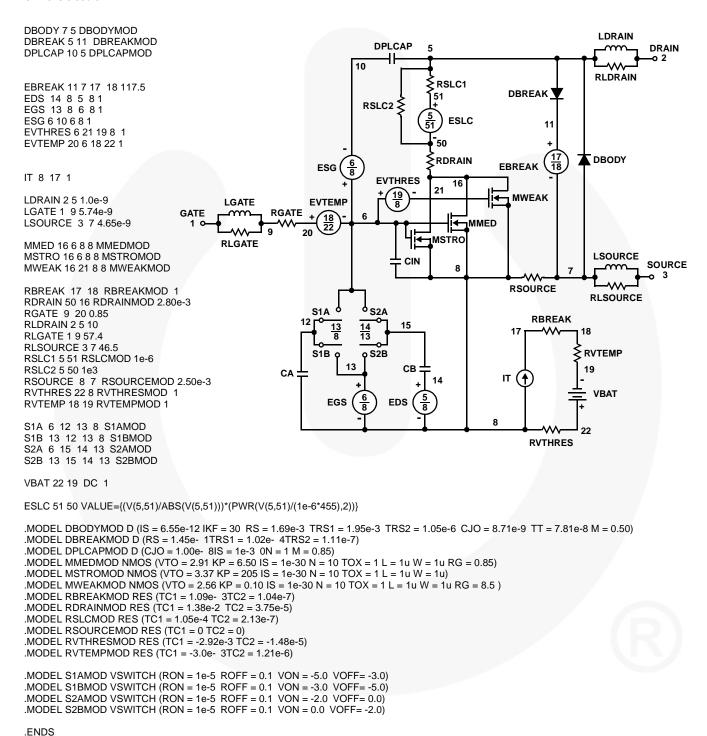


FIGURE 19. SWITCHING TIME WAVEFORM

PSPICE Electrical Model

.SUBCKT HUF75652 2 1 3; rev 11 May 1999

CA 12 8 11.0e-9 CB 15 14 11.4e-9 CIN 6 8 6.95e-9



NOTE: For further discussion of the PSPICE model, consult **A New PSPICE Sub-Circuit for the Power MOSFET Featuring Global Temperature Options**; IEEE Power Electronics Specialist Conference Records, 1991, written by William J. Hepp and C. Frank Wheatley.

SABER Electrical Model

```
REV 11 May 1999
template ta75652 n2,n1,n3
electrical n2,n1,n3
var i iscl
d..model dbodymod = (is = 6.55e-12, cjo = 8.71e-9, tt = 7.81e-8, m = 0.50)
d..model dbreakmod = ()
d..model dplcapmod = (cjo = 1.0e-8, is = 1e-30, n=1, m = 0.85)
m..model mmedmod = (type=_n, vto = 2.91, kp = 6.5, is = 1e-30, tox = 1)
m..model mstrongmod = (type=_n, vto = 3.37, kp = 205, is = 1e-30, tox = 1)
m..model mweakmod = (type=_n, vto = 2.56, kp = 0.1, is = 1e-30, tox = 1)
                                                                                                                               LDRAIN
sw_vcsp..model s1amod = (ron = 1e-5, roff = 0.1, von = -5, voff = -3)
                                                                                 DPLCAP
                                                                                                                                          DRAIN
sw_vcsp..model s1bmod = (ron = 1e-5, roff = 0.1, von = -3, voff = -5)
sw_vcsp..model s2amod = (ron = 1e-5, roff = 0.1, von = -2, voff = 0)
                                                                             10
                                                                                                                              RLDRAIN
sw_vcsp..model s2bmod = (ron = 1e-5, roff = 0.1, von = 0, voff = -2)
                                                                                              RSLC1
                                                                                                          RDBREAK
c.ca n12 n8 = 11.0e-9
                                                                               RSLC2 €
                                                                                                                   72
c.cb n15 n14 = 11.4e-9
                                                                                                                               RDBODY
                                                                                                ISCL
c.cin n6 n8 = 6.95e-9
                                                                                                           DBREAK _
d.dbody n7 n71 = model=dbodymod
                                                                                              RDRAIN
d.dbreak n72 n11 = model=dbreakmod
                                                                           6
8
                                                                     ESG
                                                                                                                    11
d.dplcap n10 n5 = model=dplcapmod
                                                                                  EVTHRES
                                                                                                 16
                                                                                              21
                                                                                     1<u>9</u>
8
                                                                                                             MWEAK
i.it n8 n17 = 1
                                                                    EVTEMP
                                                  LGATE
                                                                                                                               DBODY
                                                            RGATE
                                         GATE
                                                                                                              EBREAK
I.ldrain n2 n5 = 1e-9
                                                                                                   MMED
                                                                  20
1.1gate n1 n9 = 5.74e-9
                                                                                          I<del><</del>_MSTR
                                                  RLGATE
I.Isource n3 n7 = 4.65e-9
                                                                                                                              LSOURCE
                                                                                        CIN
                                                                                                                                         SOURCE
                                                                                                  8
m.mmed n16 n6 n8 n8 = model=mmedmod, l=1u, w=1u
m.mstrong n16 n6 n8 n8 = model=mstrongmod, l=1u, w=1u
                                                                                                             RSOURCE
m.mweak n16 n21 n8 n8 = model=mweakmod, l=1u, w=1u
                                                                                                                             RLSOURCE
                                                                               S2A
res.rbreak n17 n18 = 1, tc1 = 1.09e-3, tc2 = 1.04e-7
                                                                                                                 RBREAK
res.rdbody n71 n5 = 1.69e-3, tc1 = 1.95e-3, tc2 = 1.05e-6
                                                                                                             17
res.rdbreak n72 n5 = 1.45e-1, tc1 = 1.02e-4, tc2 = 1.11e-7
                                                                                                                            RVTEMP
res.rdrain n50 n16 = 2.80e-3, tc1 = 1.38e-2, tc2 = 3.75e-5
                                                                               o S2B
res.rgate n9 n20 = 0.85
                                                                                       CB
                                                              CA
res.rldrain n2 n5 = 10
                                                                                                            ΙT
res.rlgate n1 n9 = 57.4
                                                                                                                              VBAT
res.rlsource n3 n7 = 46.5
                                                                        EGS
                                                                                    EDS
res.rslc1 n5 n51 = 1e-6, tc1 = 1.05e-4, tc2 = 2.13e-7
                                                                                                          8
res.rslc2 n5 n50 = 1e3
res.rsource n8 n7 = 2.50e-3, tc1 = 0, tc2 = 0
                                                                                                                 RVTHRES
res.rvtemp n18 n19 = 1, tc1 = -3.0e-3, tc2 = 1.21e-6
res.rvthres n22 n8 = 1, tc1 = -2.92e-3, tc2 = -1.48e-5
spe.ebreak n11 n7 n17 n18 = 117.5
spe.eds n14 n8 n5 n8 = 1
spe.egs n13 n8 n6 n8 = 1
spe.esg n6 n10 n6 n8 = 1
spe.evtemp n20 n6 n18 n22 = 1
spe.evthres n6 n21 n19 n8 = 1
sw_vcsp.s1a n6 n12 n13 n8 = model=s1amod
sw_vcsp.s1b n13 n12 n13 n8 = model=s1bmod
sw_vcsp.s2a n6 n15 n14 n13 = model=s2amod
sw_vcsp.s2b n13 n15 n14 n13 = model=s2bmod
v.vbat n22 n19 = dc=1
equations {
i (n51->n50) +=iscl
iscl: v(n51,n50) = ((v(n5,n51)/(1e-9+abs(v(n5,n51))))*((abs(v(n5,n51)*1e6/455))**2))
```

SPICE Thermal Model

REV 1April 1999

HUF75652T

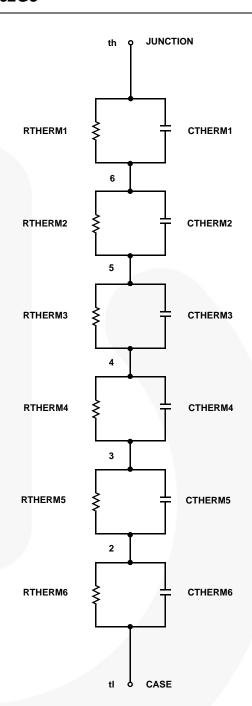
CTHERM1 th 6 9.75e-3
CTHERM2 6 5 3.90e-2
CTHERM3 5 4 2.50e-2
CTHERM4 4 3 2.95e-2
CTHERM5 3 2 6.55e-2
CTHERM6 2 tl 12.55

RTHERM1 th 6 1.96e-3
RTHERM2 6 5 4.89e-3
RTHERM3 5 4 1.38e-2
RTHERM4 4 3 7.73e-2
RTHERM5 3 2 1.17e-1
RTHERM6 2 tl 1.55e-2

SABER Thermal Model

SABER thermal model HUF75652T

```
template thermal_model th tl thermal_c th, tl \{ ctherm.ctherm1 th 6=9.75e-3 ctherm.ctherm2 6.5=3.90e-2 ctherm.ctherm3 5.4=2.50e-2 ctherm.ctherm4 4.3=2.95e-2 ctherm.ctherm5 3.2=6.55e-2 ctherm.ctherm6 2.tl=12.55 rtherm.rtherm1 th 6=1.96e-3 rtherm.rtherm2 6.5=4.89e-3 rtherm.rtherm3 5.4=1.38e-2 rtherm.rtherm4 4.3=7.73e-2 rtherm.rtherm5 3.2=1.17e-1 rtherm.rtherm6 2.tl=1.55e-2
```





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